

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application Serial No. 09/652,550
Filing Date August 31, 2000
Inventor Keiji Jono et al.
Assignee Micron Technology, Inc.
Group Art Unit..... 2811
Examiner Quang D. Vu
Attorney's Docket No. KM1-001
Title Methods of Forming an Isolation Trench in a Semiconductor, Methods of Forming an Isolation Trench in a Surface of a Silicon Wafer, Methods of Forming an Isolation Trench-Isolated Transistor, Trench-Isolated Transistor, Trench Isolation Structures Formed in a Semiconductor, Memory Cells and DRAMS

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

References -- See Attached Form PTO-1449

The attached form PTO-1449 is submitted in compliance with 37 CFR §1.56. Copies of the cited art are included. No admission is made regarding whether all the submitted references are prior art.

Respectfully submitted,

Dated: 6-30-04

By: 

Mark S. Matkin
Reg. No. 32,268

Form PTO-1449

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICELIST OF ART CITED BY APPLICANT
(Use several sheets if necessary)ATTY. DOCKET NO.
KM1-001SERIAL NO.
09/652,550

APPLICANT: Keiji Jono et al.

FILING DATE
August 31, 2000GROUP
2811

U.S. PATENT DOCUMENTS

*Examiner's Initials		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	AA	5,915,191	06/1999	Jun	438	431	
	AB	6,087,705	07/2000	Gardner et al.	257	510	
	AC	6,355,540 B1	03/2002	Wu	438	433	
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						

FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
	AJ							
	AK							
	AL							

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)

AM			
AN			
AO			
EXAMINER	DATE CONSIDERED		

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

EV 372458831



EL979953133

THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application Serial No. 09/652,550
Filing Date August 31, 2000
Inventor Keiji Jono et al.
Assignee KMT Semiconductor, LTD and Micron Technology, Inc.
Group Art Unit 2811
Examiner Quang D. Vu
Attorney's Docket No. KM1-001
Title: Methods of Forming an Isolation Trench in a Semiconductor, Methods of
Forming an Isolation Trench in a Surface of a Silicon Wafer, Methods of
Forming an Isolation Trench-Isolated Transistor, Trench-Isolated Transistor,
Trench Isolation Structures Formed in a Semiconductor, Memory Cells and
DRAMS

COPY

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

References -See Attached Form PTO-1449

The Examiner's attention is directed to the references which are listed on the attached Form PTO-1449, copies of which are attached. No admission is made regarding whether all the submitted references are prior art.

Citation of the referenced art is respectfully requested.

Respectfully submitted,

Dated: 2-2-04

By: D. Brent Kenady
D. Brent Kenady
Reg. No. 40,045

EV372458831

Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. KM1-001		SERIAL NO. 09/652,550		
 <p>LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)</p>		APPLICANT: Keiji Jono et al.						
		FILING DATE August 31, 2000		GROUP 2811				
U.S. PATENT DOCUMENTS								
*Examiner Initial		Document Number	Date	Name		Class	Subclass	Filing Date If Appropriate
	AA	6,081,662	06/27/00	Murakami et al.				
	AB	5,994,198	11/30/99	Hsu et al.				
	AC							
	AD							
	AE							
	AF							
	AG							
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FOREIGN PATENT DOCUMENTS								
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	AL						Yes	No
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	AN							
	AO							
	AP							
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)								
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Group Art Unit 2811
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Citation of the referenced art is respectfully requested.

Respectfully submitted,

Dated: 3-10-03

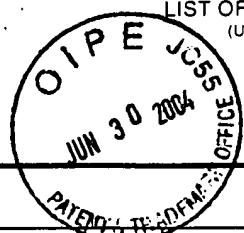
By: 

D. Brent Kenady
Reg. No. 40,045

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Form PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. KM1-001	SERIAL NO. 09/652,550
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)		APPLICANT: Keiji Jono et al.	
		FILING DATE August 31, 2000	GROUP 2811



U.S. PATENT DOCUMENTS						
Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
AA	6,034,409	03/07/2000	Sakai et al.			
AB	6,171,924 B1	01/09/2001	Wang et al.			
AC	6,154,417	11/28/2000	Kim			
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AK						

FOREIGN PATENT DOCUMENTS						
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